

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S12	1022	257/350.ccls. and @ad<"20030416"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 16:28
S10	490	(257/395-397).ccls. and @ad<"20030416"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 18:12
S13	175	(257/395-397).ccls. and @ad<"20030416" and edge	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 18:16
S15	458	(257/500 or 257/501).ccls. and @ad<"20030416"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 18:16
S4	760	semiconductor and (high adj voltage) and (low adj voltage) and ((recess or groove or trench or LOCOS) same (edge or bird or beak)) and (isolation or insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 18:33
S16	903	semiconductor and (high adj voltage) and (low adj voltage) and ((recess or groove or trench or LOCOS) same (edge or bird\$5 or beak)) and (isolation or insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 18:34
S17	158	semiconductor and (high adj voltage) and (low adj voltage) and ((recess or groove or trench or LOCOS) same ((edge or bird\$5 or beak) with (extend\$5 or protrud\$5 or project\$3 or bump\$4))) and (isolation or insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 18:36